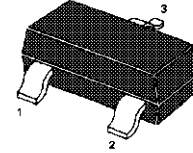


# MMBT8550C / MMBT8550D (1.5A)

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into two groups, C and D, according to its DC current gain. As complementary type the NPN transistor MMBT8050C and MMBT8050D (1.5A) is recommended.

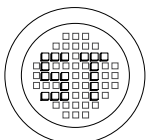


1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

	Symbol	Value	Unit
Collector Emitter Voltage	$-V_{CEO}$	25	V
Collector Base Voltage	$-V_{CBO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Peak Collector Current	$-I_{CM}$	1.5	A
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_s$	-55 to +150	$^\circ\text{C}$



®

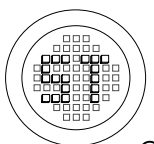
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# MMBT8550C / MMBT8550D (1.5A)

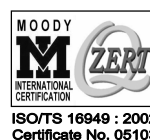
## Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Max.	Unit
DC Current Gain				
at $-V_{CE}=1\text{V}$ , $-I_C=100\text{mA}$	MMBT8550C $h_{FE}$	120	250	-
	MMBT8550D $h_{FE}$	160	400	-
at $-V_{CE}=1\text{V}$ , $-I_C=800\text{mA}$	$h_{FE}$	40	-	-
Collector Cutoff Current				
at $-V_{CB}=35\text{V}$	$-I_{CBO}$	-	100	nA
Emitter Cutoff Current				
at $-V_{BE}=6\text{V}$	$-I_{EBO}$	-	100	nA
Collector Saturation Voltage				
at $-I_C=800\text{mA}$ , $-I_B=80\text{mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Saturation Voltage				
at $-I_C=800\text{mA}$ , $-I_B=80\text{mA}$	$-V_{BE(sat)}$	-	1.2	V
Collector Emitter Breakdown Voltage				
at $-I_C=2\text{mA}$	$-V_{(BR)CEO}$	25	-	V
Collector Base Breakdown Voltage				
at $-I_C=100\mu\text{A}$	$-V_{(BR)CBO}$	40	-	V
Emitter Base Breakdown Voltage				
at $-I_E=100\mu\text{A}$	$-V_{(BR)EBO}$	6	-	V
Base Emitter Voltage				
at $-I_C=10\text{mA}$ , $-V_{CE}=1\text{V}$	$-V_{BE}$	-	1	V
Gain Bandwidth Product				
at $-V_{CE}=10\text{V}$ , $-I_C=50\text{mA}$	$f_T$	120	-	MHz



**SEMTECH ELECTRONICS LTD.**

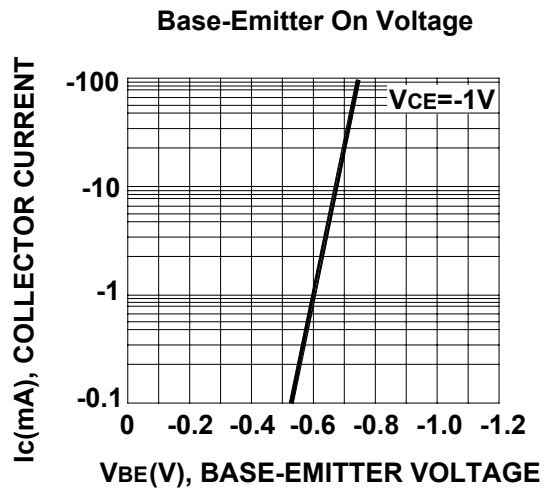
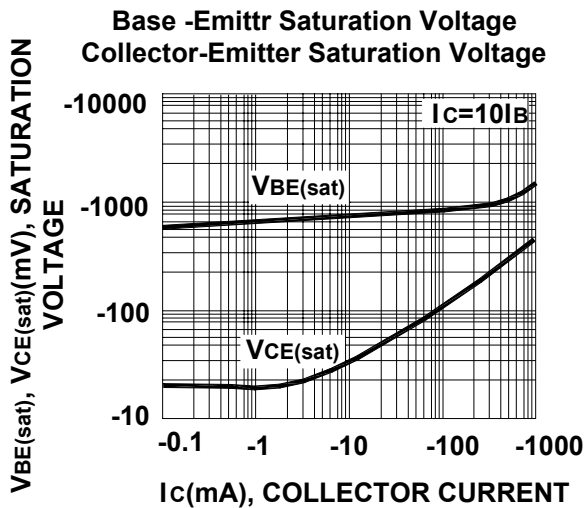
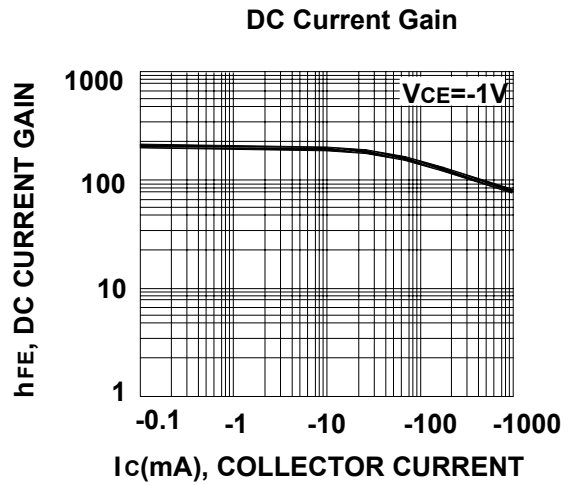
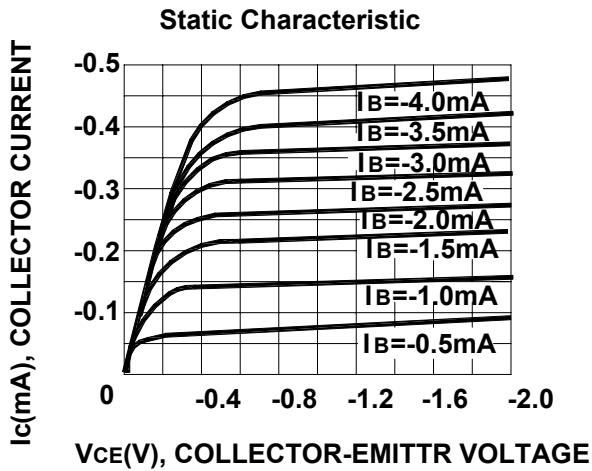
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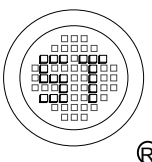
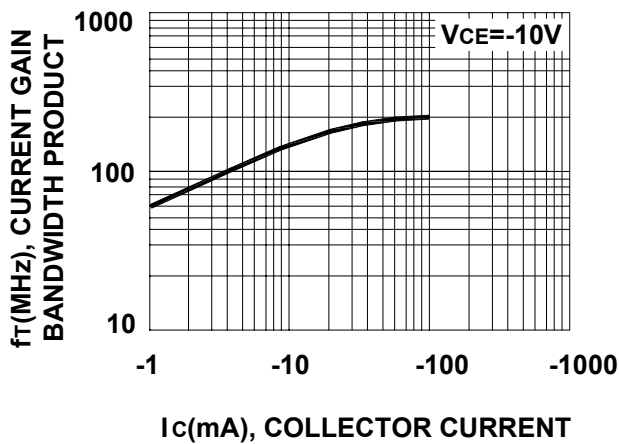
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# MMBT8550C / MMBT8550D (1.5A)

## Typical Characteristics

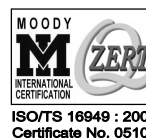


### Current Gain Bandwidth Product



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